 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  LIST OF REFERENCES CITED BY APPLICANT MAR 14 2003				ATTY DOCKET NO. 210148US99	SERIAL NO. 09/885,409		
				APPLICANT Jamal RAMDANI, et al.			
				FILING DATE June 21, 2001	GROUP 2812		
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	3,802,967	04/09/74	Ladany et al.			
	AB	4,174,422	11/13/79	Matthews et al.			
	AC	4,404,265	09/13/83	Manasevit			
	AD	4,482,906	11/13/84	Hovel et al.			
	AE	4,523,211	06/11/85	Morimoto et al.			
	AF	4,661,176	04/28/87	Manasevit			
	AG	4,793,872	12/27/88	Meunier et al.			
	AH	4,846,926	07/11/89	Kay et al.			
	AJ	4,855,249	08/08/89	Akasaki et al.			
	AI	4,891,091	01/02/90	Shastry			
	AK	4,912,087	03/27/90	Aslam et al.			
	AL	4,928,154	05/22/90	Umeno et al.			
	AM	4,963,949	10/16/90	Wanlass et al.			
	AN	5,141,894	08/25/92	Bisaro et al.			
	AO	5,159,413	10/27/92	Calviello et al.			
	AP	5,173,474	12/22/92	Connell et al.			
	AQ	5,221,367	06/22/93	Chisholm et al.			
	AR	5,225,031	07/06/93	McKee et al.			
	AS	5,358,925	10/25/94	Neville Connell et al.			
	AT	5,393,352	02/28/95	Summerfelt			
	AU	5,418,216	05/23/95	Fork			
	AV	5,450,812	09/19/95	McKee et al.			
	AW	5,478,653	12/26/95	Guenzer			
	AX	5,482,003	01/09/96	McKee et al.			
	AY	5,514,484	05/07/96	Nashimoto			
	AZ	5,556,463	09/17/96	Guenzer			
	BA	5,588,995	12/31/96	Sheldon			
	BB	5,670,798	09/23/97	Schetzina			
	BC	5,733,641	03/31/98	Fork et al.			
	BD	5,735,949	04/07/98	Mantl et al.			
	BE	5,741,724	04/21/98	Ramdani et al.			
	BF	5,810,923	09/22/98	Yano et al.			
	BG	5,830,270	11/03/98	McKee et al.			
	BH	5,912,068	06/15/99	Jia			
	BI	6,020,222	02/01/00	Wollesen			
	BJ	6,045,626	04/04/00	Yano et al.			
	BK	6,064,078	05/16/00	Northrup et al.			
	BL	6,064,092	05/16/00	Park			
	BM	6,096,584	08/01/00	Ellis-Monaghan et al.			
	BN	6,103,008	08/15/00	McKee et al.			
	BO	6,136,666	10/24/00	So			
	BP	6,174,755	01/16/01	Manning			
	BQ	6,180,486	01/30/01	Leobandung et al.			

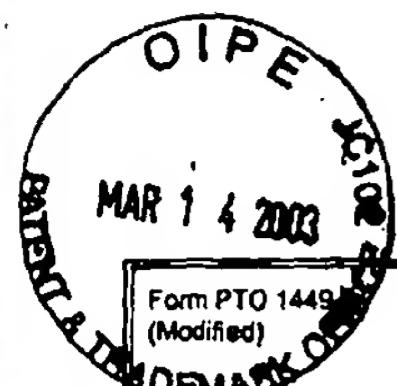
Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 210148US99	SERIAL NO. 09/885,409
<b>LIST OF REFERENCES CITED BY APPLICANT</b> <i>B2 MAR 1 6 2003</i>		APPLICANT		Jamal RAMDANI, et al.	
		FILING DATE		GROUP	
		June 21, 2001		2812	
U.S. PATENT DOCUMENTS					
EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
	GA 3,766,370	10/16/73	Walther		
	CB 4,006,989	02/08/77	Andringa		
	CC 4,284,329	08/18/81	Smith et al.		
	CD 4,777,613	10/11/98	Shahan et al.		
	CE 4,802,182	01/31/89	Thornton et al.		
	CF 4,882,300	11/21/89	Inoue et al.		
	CG 4,896,194	01/23/90	Suzuki		
	CH 4,999,842	03/12/91	Huang et al.		
	CI 5,081,062	01/14/92	Vasudev et al.		
	CJ 5,155,658	10/13/92	Inam et al.		
	CK 5,248,564	09/28/93	Ramesh		
	CL 5,260,394	11/09/93	Tazaki et al.		
	CM 5,270,298	12/14/93	Ramesh		
	CN 5,286,985	02/15/94	Taddiken		
	CO 5,310,707	05/10/94	Oishi et al.		
	CP 5,326,721	07/05/94	Summerfelt		
	CQ 5,404,581	04/04/95	Honjo		
	CR 5,418,389	05/23/95	Watanabe		
	CS 5,436,759	07/25/95	Dijaii et al.		
	CT 5,576,879	11/19/96	Nashimoto		
	CU 5,606,184	02/25/97	Abrokwah, et al.		
	CV 5,640,267	06/17/97	May et al.		
	CW 5,674,366	10/07/97	Hayashi et al.		
	CX 5,729,641	03/17/98	Chandonnet et al.		
	CY 5,790,583	08/04/98	Ho		
	CZ 5,825,799	10/20/98	Ho et al.		
	DA 5,857,049	01/05/99	Beranek et al.		
	DB 5,874,860	02/23/99	Brunel et al.		
	DC 5,926,496	07/20/99	Ho et al.		
	DD 5,937,285	08/10/99	Abrokwah, et al.		
	DE 5,981,400	11/09/99	Lo		
	DF 5,990,495	11/23/99	Ohba		
	DG 6,002,375	12/14/99	Corman et al.		
	DH 6,008,762	12/28/99	Nghiem		
	DI 6,055,179	04/25/00	Koganei et al.		
	DJ 6,107,653	08/22/00	Fitzgerald		
	DK 6,113,690	09/05/00	Yu et al.		
	DL 6,114,996	09/05/00	Nghiem		
	DM 6,121,642	09/19/00	Newns		
	DN 6,128,178	10/03/00	Newns		
	DO 6,143,072	11/07/00	McKee et al.		
	DP 6,184,144	02/06/01	Lo		
	DQ 6,222,654	04/24/01	Frigo		

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LIST OF REFERENCES CITED BY APPLICANT MAR 14 2003		APPLICANT Jamal RAMDANI, et al.	
		FILING DATE June 21, 2001	GROUP 2812

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
EA	4,484,332	11/20/84	Hawrylo			
EB	4,815,084	03/21/89	Scifres et al.			
EC	4,876,219	10/24/89	Eshita et al.			
ED	4,963,508	10/16/90	Urmeno et al.			
EE	5,060,031	10/22/91	Abrokwah, et al.			
EF	5,063,166	11/05/91	Mooney et al.			
EG	5,116,461	05/26/92	Lebby et al.			
EH	5,127,067	06/30/92	Delcoco et al.			
EI	5,144,409	09/01/92	Ma			
EJ	5,293,050	03/08/94	Chapple-Sokol et al			
EK	5,356,831	10/18/94	Calviello et al.			
EL	5,391,515	02/21/95	Kao et al.			
EM	5,442,191	08/15/95	Ma			
EN	5,444,016	08/22/95	Abrokwah, et al.			
EO	5,480,829	01/02/96	Abrokwah, et al.			
EP	5,528,414	06/18/96	Oakley			
EQ	5,614,739	03/25/97	Abrokwah et al.			
ER	5,729,394	03/17/98	Sevier et al.			
ES	5,731,220	03/24/98	Tsu et al.			
ET	5,764,676	06/09/98	Paoli et al.			
EU	5,777,762	07/07/98	Yamamoto			
EV	5,778,018	07/07/98	Yoshikawa et al.			
EW	5,778,116	07/07/98	Tomich			
EX	5,801,105	09/01/98	Yano et al.			
EY	5,828,080	10/27/98	Yano et al.			
EZ	5,858,814	01/12/99	Goossen et al.			
FA	5,861,966	01/19/99	Ortel			
FB	5,883,996	03/16/99	Knapp et al.			
FC	5,995,359	11/30/99	Klee et al.			
FD	6,058,131	05/02/00	Pan			
FE	6,137,603	10/24/00	Henmi			
FF	6,146,906	11/14/00	Inoue et al.			
FG	6,173,474	01/16/01	Conrad			
FH	6,180,252	01/30/01	Farrell et al.			
FI	4,242,595	12/30/0	Lehovec			
FJ	4,398,342	08/16/83	Pitt et al.			
FK	4,424,589	01/03/84	Thomas et al.			
FL	4,876,208	10/24/89	Gustafson et al.			
FM	4,482,422	11/84	McGinn et al.			
FN	4,667,088	05/19/87	Kramer			
FO	4,772,929	09/20/88	Manchester et al.			
FP	4,841,775	06/27/89	Ikeda et al.			
FQ	4,845,044	07/04/89	Ariyoshi et al.			

Form PTO 1449 MAY 1992 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 210148US99		SERIAL NO. 09/885,409	
LIST OF REFERENCES CITED BY APPLICANT  MAR 14 2003 B. PATENT & TRADEMARK OFFICE OTPE		APPLICANT Jamal RAMDANI, et al.			
		FILING DATE June 21, 2001		GROUP 2812	
U.S. PATENT DOCUMENTS					
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
	GA 4,868,376	09/19/89	Lessin et al.		
	GB 4,885,376	12/05/89	Verkade		
	GC 4,888,202	12/89	Murakami et al.		
	GD 4,891,091	12/90	Wanlass et al.		
	GE 5,051,790	09/24/91	Hammer		
	GF 5,055,445	10/08/91	Belt et al.		
	GG 5,081,519	11/14/92	Nishimura et al.		
	GH 5,143,854	09/01/92	Pirrung et al.		
	GI 5,185,589	02/09/93	Krishnaswamy et al.		
	GJ 5,191,625	03/02/93	Gustavsson		
	GK 5,194,397	03/16/93	Cook et al.		
	GL 5,208,182	05/04/93	Narayan et al.		
	GM 5,216,729	06/01/93	Berger et al.		
	GN 5,314,547	05/24/94	Heremans et al.		
	GO 5,352,926	10/04/94	Andrews		
	GP 5,356,509	10/18/94	Terranova et al.		
	GQ 5,371,734	12/06/94	Fischer		
	GR 5,372,992	12/94	Itozaki et al.		
	GS 5,405,802	04/11/95	Yamagata et al.		
	GT 5,442,561	08/15/95	Yoshizawa et al.		
	GU 5,453,727	09/26/95	Shibasaki et al.		
	GV 5,466,631	11/14/95	Ichikawa et al.		
	GW 5,473,047	12/05/95	Shi		
	GX 5,473,171	12/95	Summerfelt		
	GY 5,479,033	12/26/95	Baca et al.		
	GZ 5,486,406	01/23/96	Shi		
	HA 5,491,461	02/13/96	Partin et al.		
	HB 5,492,859	02/20/96	Sakaguchi et al.		
	HC 5,494,711	02/27/96	Takeda et al.		
	HD 5,504,035	04/02/96	Rostoker et al.		
	HE 5,504,183	04/02/96	Shi		
	HF 5,511,238	04/23/96	Bayraktaroglu		
	HG 5,512,773	04/96	Wolf et al.		
	HH 5,515,047	05/07/96	Yamakido et al.		
	HI 5,515,810	05/14/96	Yamashita et al.		
	HJ 5,519,235	05/96	Ramesh		
	HK 5,549,977	08/96	Jin et al.		
	HL 5,551,238	09/03/96	Prueitt		
	HM 5,552,547	09/03/96	Shi		
	HN 5,589,284	12/31/96	Summerfelt et al.		
	HO 5,602,418	02/11/97	mai et al.		
	HP 5,633,724	05/27/97	King et al.		

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 210148US99	SERIAL NO. 09/885,409				
LIST OF REFERENCES CITED BY APPLICANT <i>MAR 16 2003</i>		APPLICANT Jamal RAMDANI, et al.					
		FILING DATE June 21, 2001	GROUP 2812				
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
IA	5,650,646	07/22/97	Summerfelt				
IB	5,656,382	08/12/97	Nashimoto				
IC	5,659,180	08/19/97	Shen et al.				
ID	5,661,112	08/26/97	Hatta et al.				
IE	5,679,965	11/95	Schetzina				
IF	5,725,641	03/10/98	MacLeod				
IG	5,745,631	04/28/98	Reinker				
IH	5,776,621	07/07/98	Nashimoto				
II	5,777,350	07/07/98	Nakamura et al.				
IJ	5,789,845	08/04/98	Wadaka et al.				
IK	5,792,569	08/11/98	Sun et al.				
IL	5,792,679	08/11/98	Nakato				
IM	5,796,648	08/18/98	Kawakubo et al.				
IN	5,801,072	09/01/98	Barber				
IO	5,812,272	09/22/98	King et al.				
IP	5,814,583	09/98	Itozaki et al.				
IQ	5,825,055	10/20/98	Summerfelt				
IR	5,827,755	10/27/98	Yonchara et al.				
IS	5,833,603	11/10/98	Kovacs et al.				
IT	5,838,035	11/17/98	Ramesh				
IU	5,844,260	12/01/98	Ohori				
IV	5,846,846	12/08/98	Suh et al.				
IW	5,863,326	01/26/99	Nause et al.				
IX	5,872,493	02/16/99	Ella				
IY	5,879,956	03/99	Seon et al.				
IZ	5,880,452	03/09/99	Plesko				
JA	5,883,564	03/16/99	Partin				
JB	5,907,792	05/25/99	Droopad et al.				
JC	5,937,274	08/10/99	Kondow et al.				
JD	5,948,161	09/07/99	Kizuki				
JE	5,959,879	09/28/99	Koo				
JF	5,966,323	10/99	Chen et al.				
JG	5,987,011	11/16/99	Toh				
JH	6,022,140	02/08/00	Fraden et al.				
JI	6,022,410	02/08/00	Yu et al.				
JJ	6,023,082	02/08/00	McKee et al.				
JK	6,028,853	02/22/00	Haartsen				
JL	6,049,702	04/11/00	Tham et al.				
JM	6,078,717	06/20/00	Nashimoto et al				
JN	6,088,216	07/00	Laibowitz et al.				
JO	6,090,659	07/00	Laibowitz et al.				
JP	6,107,721	08/22/00	Lakin				
JQ	6,153,010	11/28/00	Kiyoku et al				

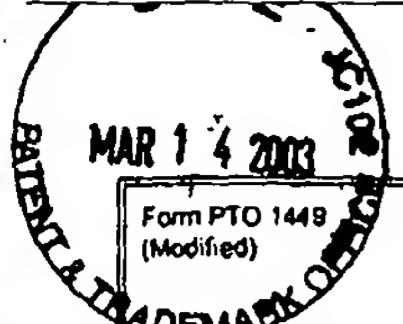


SHEET 6 OF 23

Form PTO 1449 (Modified)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO. 210148US99	SERIAL NO. 09/885,409
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Jamal RAMDANI, et al.	
	FILING DATE June 21, 2001	GROUP 2812	

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
KA	6,153,454	11/28/00	Krivokapic			
KB	6,191,011	02/01	Gilboa et al.			
KC	6,204,737	03/20/01	Ella			
KD	6,224,669	05/01/01	Yi et al.			
KE	6,225,051	05/01/01	Sugiyama et al.			
KF	6,241,821	06/05/01	Yu et al.			
KG	6,265,749	07/24/01	Gardner et al.			
KH	6,313,486	11/01	Kencke et al.			
KI	6,316,832	11/13/01	Tsuzuki et al.			
KJ	2002/0008234	01/02	Emrick			
KK	3,670,213	06/13/72	Nakawaga et al.			
KL	4,756,007	07/05/88	Qureshi et al.			
KM	4,773,063	09/20/88	Hunsperger et al.			
KN	5,394,489	02/28/95	Koch			
KO	5,406,202	04/11/95	Mehrgardt et al.			
KP	5,528,067	06/18/96	Farb et al.			
KQ	5,572,052	11/05/96	Kashihara et al.			
KR	5,767,543	06/16/98	Ooms et al.			
KS	6,175,497	01/16/01	Tseng et al.			
KT	6,197,503	03/06/01	Vo-Dinh et al.			
KU	6,248,459	06/19/01	Wang et al.			
KV	6,252,261	06/26/01	Usui et al.			
KW	6,255,198	07/03/01	Linthicum et al.			
KX	6,268,269	07/31/01	Lee et al.			
KY	6,291,319	09/18/01	Yu et al.			
KZ	6,316,785	11/13/01	Nunoue et al.			
LA	6,343,171	01/29/02	Yoshimura et al.			
LB	4,965,649	10/23/90	Zanio et al.			
LC	6,253,649	05/01	Kawahara et al.			
LD	6,211,096	04/01	Allman et al.			
LE	6,239,449	05/29/01	Fafard et al.			
LF	2001/0013313	08/16/01	Droopad et al.			
LG	6,184,044	02/06/01	Sone et al.			
LH	6,011,646	01/04/00	Mirkarimi et al.			
LI	5,227,196	07/13/93	Itoh			
LJ	6,150,239	11/21/00	Goesele et al.			
LK	5,441,577	08/15/95	Sasaki et al.			
LL	4,459,325	07/10/84	Nozawa et al.			
LM	4,392,297	07/12/83	Little			
LN	4,289,920	09/15/81	Hovel			
LO	5,281,834	01/25/94	Cambou et al.			
LP	4,901,133	02/13/90	Curran et al.			
LQ	5,514,904	05/07/96	Onga et al.			



SHEET 7 OF 23

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 210148US99	SERIAL NO. 09/885,409		
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Jamal RAMDANI, et al.					
		FILING DATE June 21, 2001		GROUP 2812			
U.S. PATENT DOCUMENTS							
EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BS	MA	5,553,089	09/03/96	Seki et al.			
BS	MB	5,528,057	06/18/96	Yanagase et al.			
BS	MC	6,229,159	05/08/01	Suzuki			
BS	MD	4,748,485	05/31/88	Vasudev			
BS	ME	4,984,043	01/08/91	Vinal			
BS	MF	5,754,319	05/19/98	Van De Voorde et al.			
BS	MG	6,108,125	08/22/00	Yano			
BS	MH	5,073,981	12/17/91	Giles et al.			
BS	MI	5,140,651	08/18/92	Soref et al.			
BS	MJ	5,610,744	03/11/97	Ho et al.			
BS	MK	6,362,017	03/26/02	Manabe et al.			
BS	ML	6,242,686	06/05/01	Kishimoto et al.			
BS	MM	5,689,123	11/18/97	Major et al.			
BS	MN	5,670,800	09/23/97	Nakao et al.			
BS	MO	5,067,809	11/26/91	Tsubota			
BS	MP	5,596,205	01/21/97	Reedy et al.			
BS	MQ	6,175,555	01/16/01	Hoole			
BS	MR	5,357,122	10/18/94	Okubora et al.			
BS	MS	4,084,130	04/11/78	Holton			
BS	MT	6,093,302	07/25/00	Montgomery			
BS	MU	6,372,813	04/16/02	Johnson et al.			
BS	MV	5,608,046	03/04/97	Cook et al.			
BS	MW	5,955,591	09/21/99	Imbach et al.			
BS	MX	6,022,963	02/08/00	McGall et al.			
BS	MY	6,083,697	07/04/00	Beecher et al.			
BS	MZ	5,063,081	11/05/91	Cozzette et al.			
BS	NA	5,479,317	12/26/95	Ramesh			
BS	NB	5,306,649	04/26/94	Hebert			
BS	NC	5,962,069	10/05/99	Schindler et al.			
BS	ND	5,541,422	07/30/96	Wolf et al.			
BS	NE	5,873,977	02/23/99	Desu et al.			
BS	NF	5,538,941	07/23/96	Flindikoglu et al.			
BS	NG	6,046,464	04/04/00	Schetzina			
BS	NH	6,235,145	05/22/01	Li et al.			
BS	NI	5,610,744	03/11/97	Ho et al.			
BS	NJ	5,280,013	01/18/94	Newman et al.			
BS	NK	6,348,373 B1	02/19/02	Ma et al.			
BS	NL	6,339,664 B1	01/15/02	Farjady et al.			
BS	NM	4,439,014	03/27/84	Stacy et al.			
BS	NN	4,889,402	12/26/89	Reinhart			
BS	NO	5,963,291	10/05/99	Wu et al.			
BS	NP	6,011,641	01/04/00	Shin et al.			
BS	NQ	6,340,788 B1	01/22/02	King et al.			

Form PTO 1449 (Rev. 1-2001)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 210148US99	SERIAL NO. 09/885,409	
LIST OF REFERENCES CITED BY APPLICANT  MAR 14 2003		APPLICANT		Jamal RAMDANI, et al.		
		FILING DATE		GROUP		
		June 21, 2001		2812		
U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BS	OA 5,807,440	09/15/98	Kubota et al.			
	OB 4,681,982	07/21/87	Yoshida			
	OC 4,629,821	12/16/86	Bronstein-Bonte et al.			
	OD 4,452,720	06/05/84	Harada et al.			
	OE 3,935,031	01/27/76	Adler			
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	OG 5,053,835	10/01/91	Horikawa et al.			
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AAF	0 607 435	07/27/94	EP	X
AAG	1 001 468	05/17/00	EP	X
AAH	0 514 018	11/19/92	EP	X
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AAK	11-238683	08/31/99	Japan	X
AAL	11-260835	09/24/99	Japan w/English Abstract	X
AAM	HEI 2-391	01/05/90	Japan w/English Abstract	X
AAN	5-48072	02/26/93	Japan w/English Abstract	X
AAO	52-88354	07/23/77	Japan w/English Abstract	X
AAP	54-134554	10/19/79	Japan w/English Abstract	X
AAQ	55-87424	07/02/80	Japan w/English Abstract	X
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AAW	63-198365	08/17/88	Japan w/English Abstract	X
AAX	63-321943	12/04/98	Japan	X
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ABH	1 109 212	06/20/01	Europe	
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BAB	2000-068466	03/00	Japan (Abstract)
BAC	64-50575	02/27/89	Japan
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BAF	WO 01/33585	05/10/01	WIPO
BAG	1-102435	04/20/89	Japan w/English Abstract
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BAT	WO 01/37330	05/25/01	WIPO
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BAX	0 964 453	12/15/99	Europe
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BBA	9-82913	03/28/97	Japan w/English Abstract
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BBC	EP 0 957 522	11/17/99	Europe
BBD	EP 0 810 666	12/03/97	Europe
BBE	1-179411	07/17/89	Japan w/English Abstract
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BBI	WO 01/59814 A2	08/16/01	WIPO
BBJ	WO 02/09160 A2	01/31/02	WIPO
BBK	WO 00/06812	02/10/00	WIPO
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BBM	0 538 611	04/28/93	Europe
BBN	WO 01/59820 A1	08/16/01	WIPO
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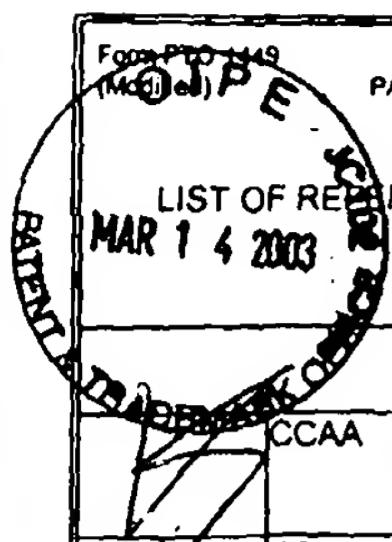
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D I P LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Jamal RAMDANI, et al.	
		FILING DATE June 21, 2001	GROUP 2812

MAR 14 2003



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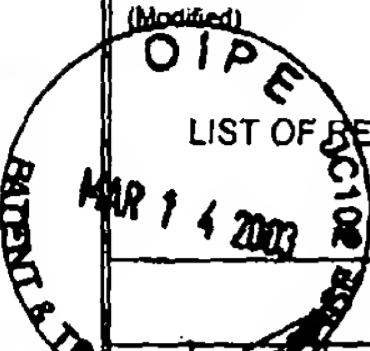
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CCAB	Suzuki et al., "A Proposal of Epitaxial Oxide Thin Film Structures For Future Oxide Electronics," <i>Materials Science and Engineering B41</i> , (1996), pp. 166-173.		
CCAC	W. F. Egelhoff et al., "Optimizing GMR Spin Valves: The Outlook for Improved Properties", 1998 Int'l Non Volatile Memory Technology Conference, pp. 34-37.		
CCAD	Wang et al., "Processing and Performance of Piezoelectric Films", Univ. Of MD, Wilcoxon Research Col, and Motorola Labs, May 11, 2000.		
CCAE	M. Rotter et al., "Nonlinear Acoustoelectric Interactions in GaAs/LiNbO <sub>3</sub> Structures", <i>Applied Physics Letters</i> , Vol. 75(7), August 16, 1999, pp. 965-967.		
CCAF	K. Sreenivas et al., "Surface Acoustic Wave Propagation on Lead Zirconate Titanate Thin Films," <i>Appl. Phys. Lett.</i> 52 (9), Feb. 29, 1998, pp. 709-711.		
CCAG	M. Rotter et al., "Single Chip Fused Hybrids for Acousto-Electric and Acousto-Optic Applications," 1997 <i>Applied Physics Letters</i> , Vol. 70(16), April 21, 1997, pp. 2097-2099.		
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CCAJ	R. Houdre et al., "Properties of GaAs on Si Grown by Molecular Beam Epitaxy," <i>Solid State and Materials Sciences</i> , Vol. 16, Issue 2, 1990, pp. 91-114.		
CCAK	S. F. Fang et al., "Gallium Arsenide and Other Compound Semiconductors on Silicon," <i>J. Appl. Phys.</i> , 68(7), October 1, 1990, pp. R31-R58.		
CCAL	Carlin et al., "Impact of GaAs Buffer Thickness on Electronic Quality of GaAs Grown on Graded Ge/GeSi/Si Substrates, <i>Appl. Phys. Letter</i> , Vol. 76, No. 14, April 2000, pp. 1884-1886.		
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*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.			

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DDAA	Abhay M. Joshi et al., "Monolithic InGaAs-on-silicon Wave Infrared Detector Arrays," <i>Intn. Society for Optical Engineering</i> , Vol. 2999, pp. 211-224.		
DDAB	Bruley et al., "Nanostructure and Chemistry of a (100)MgO/(100) GaAs Interface," <i>Appl. Phys Lett</i> , 65(5), Aug. 1994, pp. 564-566.		
DDAC	Fork et al., "Epitaxial MgO On Si(001) for Y-Ba-Cu-O Thin Film Growth by Pulsed Laser Deposition," <i>Appl. Phys Lett.</i> , 58(20), May 20, 1991, pp. 2294-2296.		
DDAD	Himpsel et al., "Dielectrics on Semiconductors," <i>Materials Science and Engineering</i> , B1(1988), pp. 9-13.		
DDAE	Li et al., "Epitaxial La <sub>0.67</sub> Sr <sub>0.33</sub> MnO <sub>3</sub> Magnetic Tunnel Junctions," <i>J. Appl. Phys.</i> 81(8), Apr. 15, 1997, pp. 5509-5511.		
DDAF	O'Donnell et al., "Colossal Magnetoresistance Magnetic Tunnel Junctions Grown by Molecular-Beam Epitaxy," <i>Appl. Physics Letters</i> , Vol. 76, No. 14, April 3, 2000, pp. 1914-1916.		
DDAG	Mikami et al., "Formation of Si Epi/MgO-Al <sub>2</sub> O <sub>3</sub> Epi./SiO <sub>3</sub> /Si and Its Epitaxial Film Quality," Fundamental Research Laboratories and Microelectronics Laboratories, pp. 31-34, 1983.		
DDAH	T. Asano et al., "An Epitaxial Si/Insulator/Si Structure Prepared by Vacuum Deposition of CaF <sub>2</sub> and Silicon," <i>Thin Solid Films</i> , Vol. 93 (1982), pp. 143-150.		
DDAI	T. Chikyow et al., "Reaction and Regrowth Control of CeO <sub>2</sub> on Si(111) Surface for the Silicon-On-Insulator Structure," <i>Appl. Phys. Lett.</i> , Vol. 65, No. 8, 22 August 1994, pp. 1030-1032.		
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DDAK	R.A. Morgan et al., "Vertical-Cavity Surface-Emitting Lasers Come of Age," <i>SPIE</i> , Vol. 2683, pp. 18-29.		
DDAL	"Technical Analysis of Qualcomm QCP-800 Portable Cellular Phone (Transmitter Circuitry)," Talus Corporation, Qualcomm QCP-800 Technical Analysis Report, December 10, 1996, pp. 5-8.		
DDAM	Jo-Ey WONG, et al.; "AN ELECTROSTATICALLY-ACTUATED MEMS SWITCH FOR POWER APPLICATIONS"; IEEE, 2000; pp. 633-638		
DDAN	T. MIZUNO, et al.; "Electron and Hole Mobility Enhancement in Strained-Si MOSFET's on SiGe-on-Insulator Substrates Fabricated by SIMOX Technology"; IEEE ELECTRON DEVICE LETTERS, VOL. 21, NO. 5, MAY 2000; pp. 230-232		
DDAO	F.M. BUFFER, et al.; "Strain-dependence of electron transport in bulk Si and deep-submicron MOSFET's" Computatural Electronics, 2000, Book of Abstracts, IWCE Glasgow 2000, 7 <sup>th</sup> Int'l Workshop on, 2000; pp. 64-65		
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DDAQ	Kihong KIM, et al." On-Chip Wireless Interconnection with Integrated Antennas"; 2000 IEEE; pp. 20.2.1-20.3.4		
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EEAE	H. Nagata, "A Preliminary Consideration of the Growth Behaviour of CeO <sub>2</sub> , SrTiO <sub>3</sub> and SrVO <sub>3</sub> Films on Si Substrate," <i>Thin Solid Films</i> , 224, 1993, pp. 1-3.		
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EEAH	H. Ishiwara et al., "Epitaxial Growth of Perovskite Type Oxide Films on Substrates"; <i>Materials Research Symposium Proceedings</i> , Vol. 220, pp. 595-600, April 29 - May 3, 1991.		
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HHAH	Wenhua Zhu et al.; "Molecular Beam Epitaxy of GaAs on Si-on-Insulator"; 320 <i>Applied Physics Letters</i> 59(1991) 8 July No. 2; pp. 210-212				
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HHAJ	J.M. Daughton et al.; "Applications of Spin Dependent Transport Materials"; <i>J. Phys. D. Appl. Phys.</i> 32(1999) R169-R177				
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SHEET 1 OF 5

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June 21, 2001

GROUP  
2812

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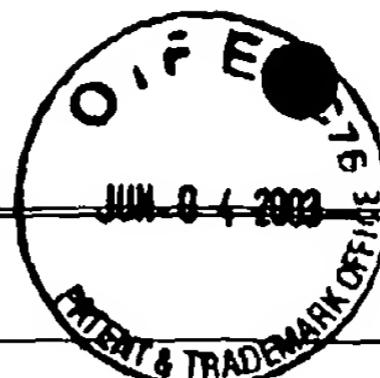
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SHEET 3 OF 5

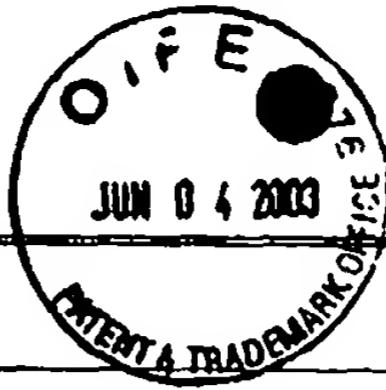


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		FILING DATE June 21, 2001	GROUP 2812

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	CBD	EP 0 860 913	08/26/95	EUROPE		
	CBE	5-232307	09/10/93	JAPAN W/ENGLISH ABSTRACT		
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SHEET 5 OF 5

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